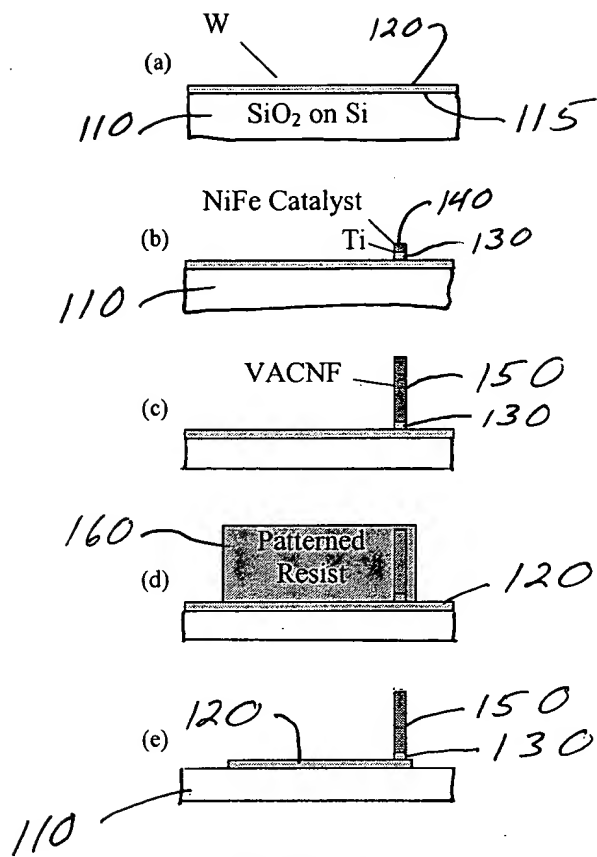


FIG. 1A-1E



Figures 1A-1E

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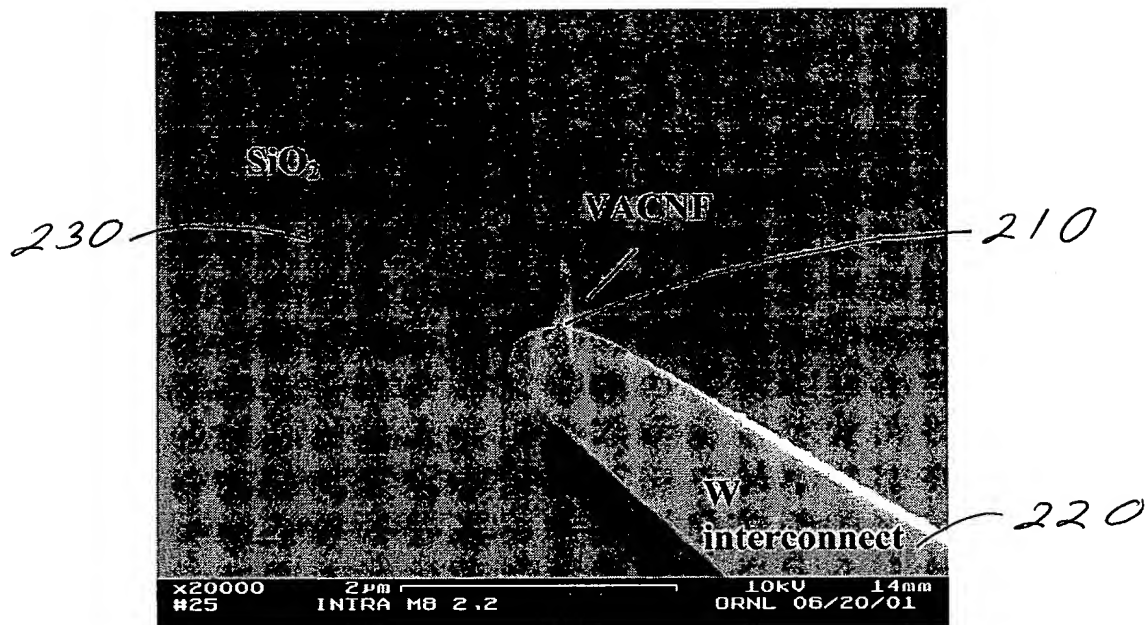


Figure 2

Figure 1 consists of five cross-sectional views (a) through (e) illustrating the fabrication of a semiconductor device.
 (a) Shows a substrate 330 with a thin SiO₂ layer 310 and a gate stack 320.
 (b) A resist layer 350 is applied over the SiO₂ layer 310.
 (c) The resist layer 350 is patterned into a central block.
 (d) The SiO₂ layer 330 is etched away from the top of the resist block 350.
 (e) The final structure with the SiO₂ layer 330 removed from the top of the resist block 350.

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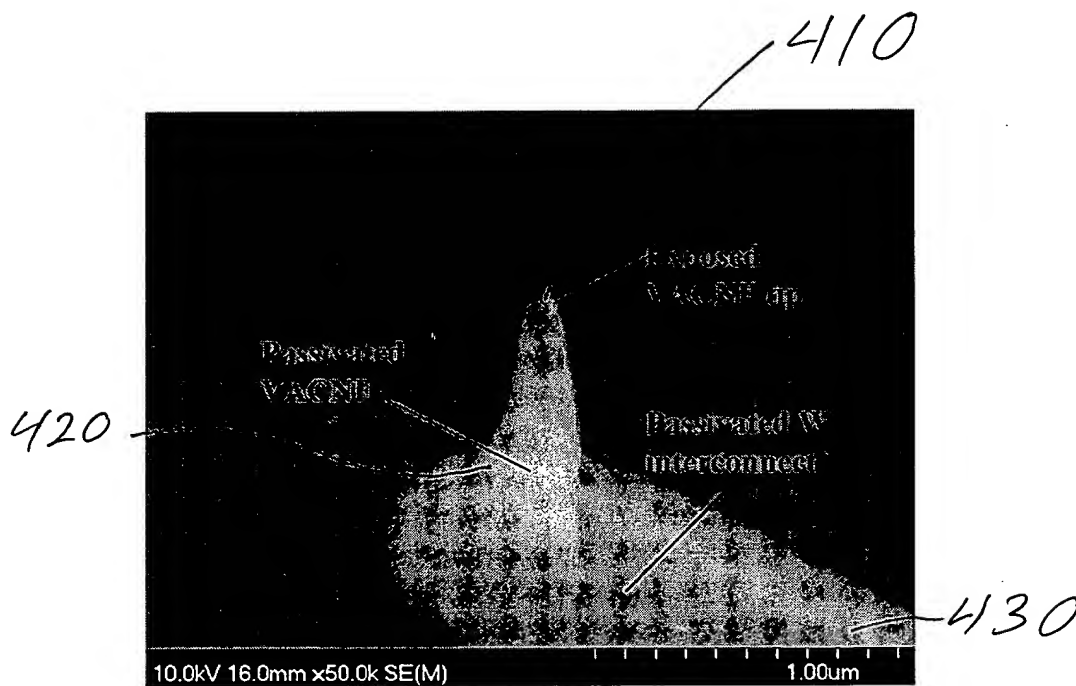


Figure 4

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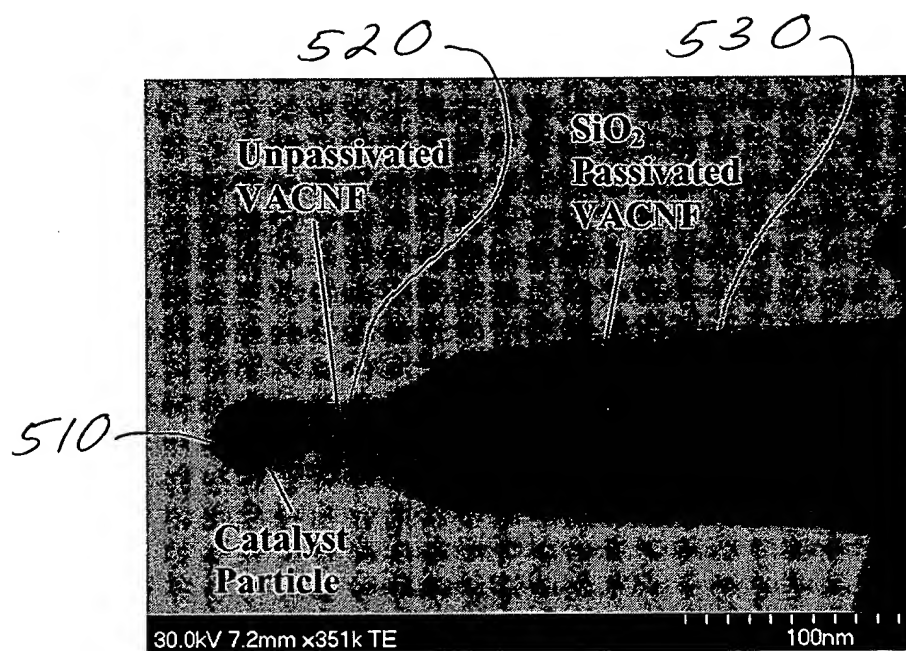


Figure 5

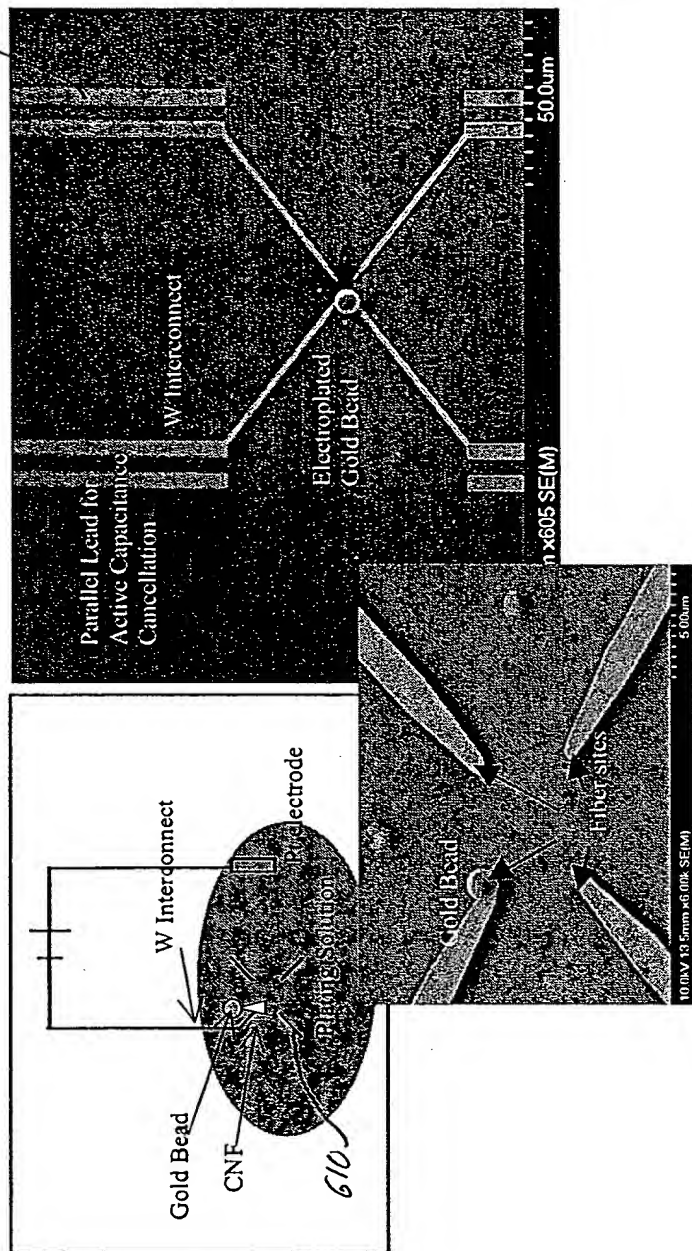


Figure 6A

Figure 6B

Figure 6C